

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application Serial No. .... 10/757,276  
Filing Date ..... January 14, 2004  
Inventor ..... Kevin L. Beaman et al.  
Assignee..... Micron Technology, Inc.  
Group Art Unit ..... 2813  
Examiner ..... Stephen W. Smoot  
Attorney's Docket No. .... MI22-2475  
Customer No. .... 021567  
Title: A Method of Forming a Structure Over a Semiconductor Substrate

**EXAMINER INTERVIEW SUMMARY OF JUNE 28, 2007**

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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Applicant's representative held an interview with Examiner Smoot on June 28, 2007.

Applicant's representative would like to thank Examiner Smoot for his time and attention to this matter.


Agreement was reached to amend dependent claim 58 for consistency. Claim 58 will be amended in the following manner by Examiner's Amendment:

58. (by Examiner amendment) The method of claim 36 further comprising forming a silicide layer over at least one of the first and second layers comprising the conductively doped silicon.

Applicant's representative is greatly appreciative of the efforts and time put in to this matter by Examiner Smoot.

Respectfully submitted,

Dated: 6-28-07

By:   
D. Brent Kenady  
Reg. No. 40,045